

Silicon NPN Power Transistors

2SC3170

DESCRIPTION

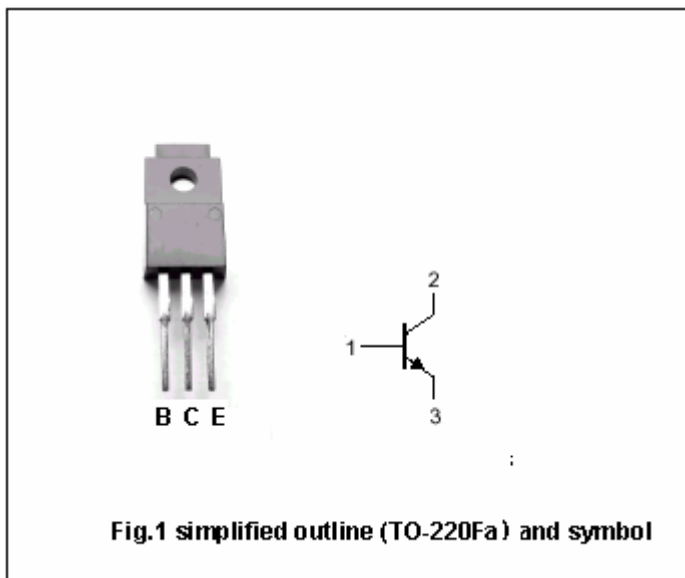
- With TO-220Fa package
- Low collector saturation voltage
- High breakdown voltage

APPLICATIONS

- For high speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		7	A
I _{CM}	Collector current-peak		15	A
P _C	Collector power dissipation	T _a =25	2	W
		T _C =25	40	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A , L=25mH	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A ; I _B =0.6A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =3A ; I _B =0.6A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μ A
h _{FE-1}	DC current gain	I _C =0.1A ; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =5V	8			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		8		MHz

Switching times

t _{on}	Turn-on time	I _C =3A ; I _{B1} =-I _{B2} =0.6A V _{CC} =100V			1.0	μ s
t _{stg}	Storage time				3.0	μ s
t _f	Fall time				1.0	μ s

PACKAGE OUTLINE

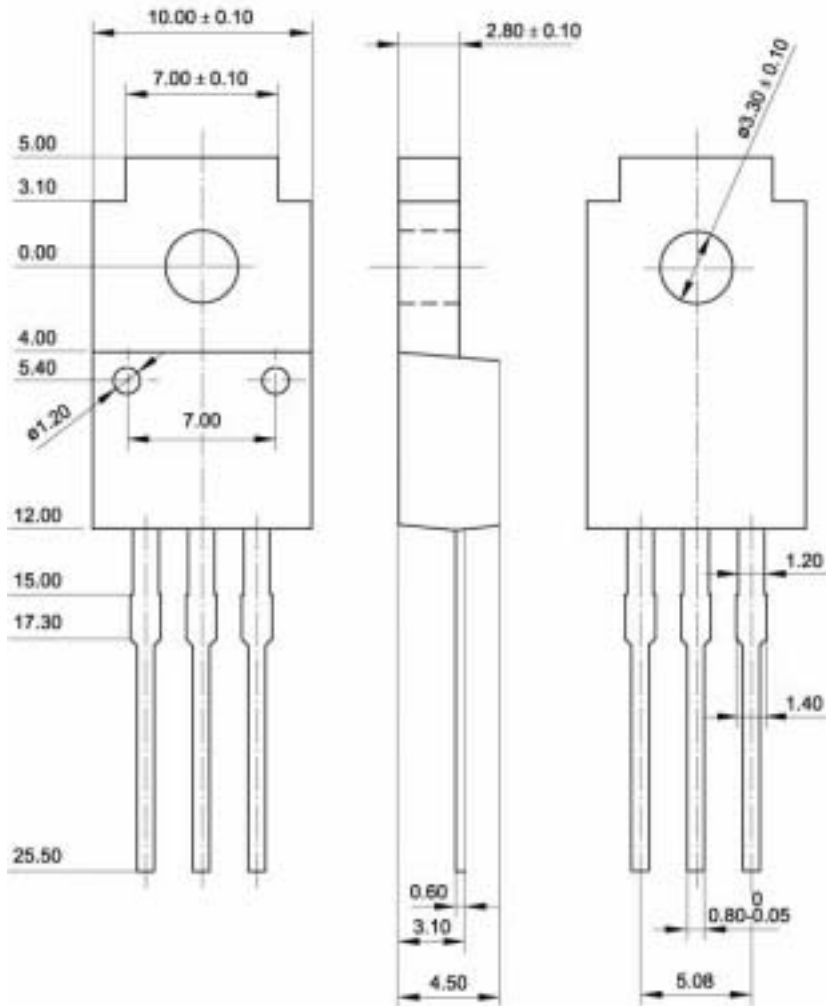


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)